

Publications that quote the use of OAR atom sources

Nitrides (AlN, GaN, InN)

1. **Evaluation of a new plasma source for molecular beam epitaxial growth of InN and GaN films.** W Hoke P Lemonias & D Weir. J Crystal Growth 111, p1024 (1991)
2. **Growth of zinc blende-GaN on b-SiC coated (001) Si by molecular beam epitaxy using a radio frequency plasma discharge, nitrogen free-radical source.** H Liu, C Frenkel, J Kim & R Park. J Appl Phys 74 (10), p6124 (1993)
3. **Substrate nitridation effects on GaN grown on GaAs substrates by molecular beam epitaxy using RF-radical nitrogen source.** A Kikuchi, H Hoshi, & K Kishino. Jpn J Appl Phys Vol 33, p688 (1994)
4. **The growth and properties of group III nitrides.** C.T. Foxon, T.S. Cheng, D.E. Lacklison, S.V.Novikov, D. Johnston, N. Baba-Ali, T.L. Tansley, J. W. Orton, S. Hooper, L.C. Jenkins, A.F. Ioffe. Proceedings of MBE-VIII, Osaka, Japan (1994).
5. **Growth by molecular beam epitaxy and electrical characterisation of Si-doped zinc blende GaN films deposited on b-SiC coated (001) Si substrates.** J.G. Kim, A.C. Frenkel, H Liu and R. M. Park. Appl. Phys. Lett. 65 (1) p91- 93 (1994)
6. **Substrate nitridation effects on GaN grown on GaAs substrates by molecular beam epitaxy using RF-radical nitrogen source.** A. Kikuchi, H. Hoshi and K. Kishino. Jpn. J. Appl. Phys. 33 p688 (1994)
7. **Selective growth of zinc-blende, wurzite, or a mixed phase of gallium nitride by molecular beam epitaxy.** T. S. Cheng, L.C. Jenkins, S. E. Hooper, C. T. Foxon, J. W. Orton, and D. E. Lacklison. Appl. Phys. Lett. 66 (12) p1509 (1995)
8. **Electrical characterisation of single barrier GaAs/GaN/GaAs heterostructures.** X. Huang, T. S. Cheng, S. E. Hooper, T. J. Foster, L. C. Jenkins, J. Wang, C. T. Foxon, J. W. Orton, L. Eaves and P. C. Main. J. Vac Sci Technol. B 13(4) p1582 (1995)
9. **Molecular beam epitaxy growth and properties of GaN films on GaN/SiC substrates.** W.C. Hughes, W.H. Rowland, Jr., M. A. L. Johnson, Shizuo Fujita, J. W. Cook, Jr and J. F. Schetzina. J. Vac. Sci. Technol. B 13(4) p1571 (1995).
10. **Photoluminescence and raman scattering from GaN layers grown on GaAs and GaP substrates.** N. N. Zinov'ev, A. V. Andrianov, B. Y. Averbukh, I. D. Yaroshetskii, T. S. Cheng, L. C. Jenkins, S. E. Hooper, C. T. Foxon, J. W. Orton. Semicond. Sci. Technol. 10 p1117(1995)
11. **Morphology of luminescent GaN films grown by molecular beam epitaxy** C.Trager-Cowan, K.P. O'Donnell, S.E.Hooper and C.T.Foxon, Appl. Phys.Lett. 68 p355 (1995)
12. **Auger electron spectroscopy, x-ray diffraction, and scanning electron microscopy of InN, GaN, and Ga(AsN) films on GaP and GaAs(001) substrates.** L.C. Jenkins, T. S. Cheng, C. T. Foxon, S. E. Hooper, J. W. Orton, S. V. Novikov and V. V. Tret'yakov. J. Vac. Sci. Tech. B13(4) p1585 (1995)
13. **The growth and properties of group III nitrides** C. T. Foxon, T. S. Cheng, S. V. Novikov, D. E. Lacklisonⁿ, L. C. Jenkins, D. Johnston, J. W. Orton, S. E. Hooper, N. Baba-Ali, T. L. Tansley¹ and V. V. Tret'yakov Journal of Crystal Growth 150 p892 (1995)
14. **Growth of GaN by gas-source molecular beam epitaxy by ammonia and by plasma generated nitrogen radicals** W. S. Wong N. Y. Li, H. K. Dong, F. Deng, S. S. Lau, C. W. Tu^r J. Hays, S. Bidnyk and J. J. Song Journal of Crystal Growth 164 p159 (1996)
15. **TEM and PL characterisation of MBE grown epitaxial GaN/GaAs** Y Xin, P.D.Brown, C.B.Boothroyd, A.R.Preston, C.J.Humphreys, T.S.Cheng, C.T. Foxon, A.V.Andrianov and J.W.Orton, Presented at Spring MRS meeting, Boston USA (1996)

16. **Plasma preconditioning of sapphire substrate for GaN epitaxy.** C. Heinlein, J. Grepstad, H. Riechert and R. Averbeck. Proceedings of E-MRS meeting Strasbourg, France (1996)
17. **Structural and optical properties of nitride-based laser diode,** H. Amano, S. Sota, T. Takeuchi, H. Sakai, I Akasaki, Proceedings III-V symposium 1996 Fall MRS meeting, Boston USA (1996)
18. **Characterisation of an RF-plasma source of active nitrogen.** C.D. Stinespring, S.Kumar, J.S.Gold, S.L.Buckowski, and T.H.Myers Proceedings III-V symposium 1996 Fall MRS meeting, Boston USA (1996)
19. **Ga desorption and growth behaviour of GaN during molecular beam epitaxy.** S. Guha, N. A. Bojarczuk, D. W. Kisker. Proceedings III-V symposium 1996 Fall MRS meeting, Boston USA (1996)
20. **A study of mixed group-V nitrides grown by gas-source MBES using a N radical beam source.** W. G. Bi, C. W. Tu. Proceedings III-V symposium 1996 Fall MRS meeting, Boston USA (1996)
21. **MBE-growth of (In)GaN for LED applications.** H. Riechert, A. Graber, M. Schienle, U. Strauss, H. Tews. Proceedings III-V symposium 1996 Fall MRS meeting, Boston USA (1996)
22. **On the kinetics of growth of highly defective GaN epilayers and the origin of the deep trap responsible for yellow-band luminescence.** H. Liu, J. G. Kim, M. H. Ludwig and R. M. Park. Appl. Phys. Lett. 71 (3) p347 (1997)
23. **Surface Morphology of GaN films determined from quantitative x-ray reflectivity.** D. Lederman, Zhonghai Yu, T. H. Myers and M. R. Richards-Babb. Appl. Phys. Lett. 71 (3) p368 (1997)
24. **Effects of substrate type on the characteristics of GaN epitaxial films grown by molecular beam epitaxy.** T. S. Cheng, C. T. Foxon, G. B. Ren, J. W. Orton, Yu. V. Melnik, I. P. Nikitina, A. E. Nikolaev, S. V. Novikov and V. A. Dmitriev. Semicond. Sci. Technol. 12 p917 (1997)
25. **Growth of self-organised GaN nanostructures on Al₂O₃ (0001) by RF-radical source molecular beam epitaxy.** M. Yoshizawa, A. Kikuchi, M. Mori, N. Fujita and K. Kishino. Jpn. J. Appl. Phys 36 p459 (1997)
26. **Effect of nitridation and buffer in GaN films grown on A-plane (11-20) sapphire.** D. Doppalapudi, E. Iliopoulos, S. N. Basu and T. D. Moustakas. Presented at Nitride semiconductors symposium 1997 Fall MRS meeting, Boston USA (1997)
27. **A TEM study of microstructural evolution in MBE growth of GaN.** D. M. Tricker, P. D. Brown, T. S. Cheng, C. T. Foxon and C. J. Humphreys. Presented at Nitride semiconductors symposium 1997 Fall MRS meeting, Boston USA (1997)
28. **Structure and properties of III-N semiconductor thin films at low temperatures by N-radical-assisted pulsed laser deposition.** F. E. Fernandez, M. Pumarol, A. Martinez and V. Pantojas. Presented at Nitride semiconductors symposium 1997 Fall MRS meeting, Boston USA (1997)
29. **Growth of GaN on lithium gallate: development of a GaN thin/compliant substrate.** W. A. Doolittle, C. Carter-Comen, S. Stock, N. M. Jokerst, R. A. Metzger, K. Lee, G. May, A. S. Brown P. Kohl and T. Kroppenwicki. Presented at Nitride semiconductors symposium 1997 Fall MRS meeting, Boston USA (1997)
30. **MBE growth of GaN on NdGaO₃ (101).** C. Fechtman, S. Einfeldt, H. Heinke, D. Hommel, T. Lukaszewicz and J. Baranowski. Presented at Nitride semiconductors symposium 1997 Fall MRS meeting, Boston USA (1997)
31. **Electron mobility in n-GaN films.** H. M. Ng, D. Doppalapudi, R. Singh and T. D. Moutakas. Presented at Nitride semiconductors symposium 1997 Fall MRS meeting, Boston USA (1997)
32. **A combined TEM/RHEED/CL study of epitaxial GaN.** D. M. Tricker, C. J. Humphreys, T. S. Cheng, C. T. Foxon, D. Evans, S. Galloway and J. Brock. Presented at Nitride semiconductors symposium 1997 Fall MRS meeting, Boston USA (1997)

33. **The effect of N incorporation in II-Vs: optical properties of InAsPN/GaNP multiple quantum wells.** X. B. Mei and C. W. Tu. Presented at Nitride semiconductors symposium 1997 Fall MRS meeting, Boston USA (1997)
34. **Ga-edge EXAFS studies of group III nitride alloys.** A. Blant, T. S. Cheng, N. Jeffs, C. T. Foxon, C. Bailey, P. G. Harrison, A. Dent and J. F. W. Mosselmanns. Presented at Nitride semiconductors symposium 1997 Fall MRS meeting, Boston USA (1997)
35. **Homoeptaxial growth of GaN under Ga-stable and N-stable conditions by RF-plasma molecular beam epitaxy.** E. J. Tarsa, B. Heying, X. H. Wu, P. Fini, S. P. DenBaars and J. S. Speck. Presented at Nitride semiconductors symposium 1997 Fall MRS meeting, Boston USA (1997)
36. **Morphology and luminescence properties of undoped GaN and AlN layers grown by MBE on Si(111) substrates.** M. A. Sánchez-García, E. Monroy, F. J. Sánchez, D. Basak, E. Calleja, A. Sanz-Hervás and C. Villar. IX European workshop on MBE, Oxford, UK (1997)
37. **Nitridation of the GaAs(001) Surface using atomic nitrogen.** P. Hill, J. Lu, D. I. Westwood and J. E. Macdonald. IX European workshop on MBE, Oxford, UK (1997)
38. **MBE growth of GaN - a study by high resolution X-ray diffraction.** H. Heinke, U. Birkle, S. Einfeldt and D. Hommel. Presented at the Second European GaN Workshop, Valbonne Sophia Antipolis, France (1997)
39. **Characterisation of aN grown by MBE using an RF nitrogen source.** J. Stemmer, J. Aderhold, J. Ackermann, D. Uffmann and J. Graul. Presented at the Second European GaN Workshop, Valbonne Sophia Antipolis, France (1997)
40. **A model for yellow band luminescence in MBE grown material.** T. Eustis, W. Schaff, M. Murphy, L. Eastman, W. A. Daves, E. Sophir and N. Weinman. Presented at the Second European GaN Workshop, Valbonne Sophia Antipolis, France (1997)
41. **Studies of Mg-doped GaN grown by MBE on GaAs(111)_B substrates.** T. S. Cheng, C. T. Foxon, N. J. Jeffs, D. J. Dewsnip, L. Flannery, J. W. Orton, S. V. Novikov, B. Y. Ber and Y. A. Kudriavtsev. Presented at the Second European GaN Workshop, Valbonne Sophia Antipolis, France (1997)
42. **Surface morphology and structure of GaN_xAs_{1-x}, x=0-1.** J. V. Thordson, O. Zsebök and T. G. Andersson. Presented at the Second European GaN Workshop, Valbonne Sophia Antipolis, France (1997)
43. **High frequency AlGaIn/GaN MODFET's.** L. Eastman, K. Chu, W. Schaff, M. Murphy, N. Wienmans and T. Eustis. Presented at the Second European GaN Workshop, Valbonne Sophia Antipolis, France (1997)
44. **Atomic ordering and phase separation in AlGaInN alloys.** T. D. Moustakas, D. Korakakis, R. Singh, D. Doppalapudi, H. M. Ng, A. Sampath, E. Iliopoulos and M. Misra. Presented at Nitride semiconductors symposium 1997 Fall MRS meeting, Boston USA (1997)
45. **Mg in GaN: Incorporation of a volatile species at high temperatures during molecular beam epitaxy.** S. Guha, N. A. Bojarczuk and F. Cardone. Appl. Phys. Lett. 71 (12) p1685 (1997)
46. **Plasma preconditioning of sapphire substrate for GaN epitaxy** C. Heinlein, J. Grepstad, H. Riechert and R. Averbeck Materials Science and Engineering B 43 p253 (1997)
47. **MBE growth and properties of GaN on GaN/SiC substrates** M. A. L. Johnson, Shizuo Fujita, W. H. Rowland, Jr, K. A. Bowers, W. C. Hughes, Y. W. He, N. A. El Masry J. W. Cook, Jr, J. F. Schetzina, J. Ren and J. A. Edmond Solid-State Electronics 41 (2) p213 (1997)
48. **Selective meltback etching of GaN layers in liquid-phase electroepitaxial technique** S.V.Novikov, T.S.Cheng, Z.Mahmood, I.Harrison and C.T.Foxon Journal of Crystal Growth 173 p1 (1997)
49. **Growth of GaN, InGaIn, and AlGaIn films and quantum well structures by molecular beam epitaxy** J. F. Schetzina, M. A. L. Johnson, W. C. Hughes, W. H. Jr. Rowland, J. W. Jr. Cook, M. Leonard, H. S. Kong, J. A. Edmond and J. Zavada Journal of Crystal Growth 175-176 p72 (1997)

50. **Shutter control method for control of Al contents in AlGaIn quasi-ternary compounds grown by RF-MBE.** Akihiko Kikuchi, Masaki Yoshizawa, Masashi Mori, Nobuhiko Fujita, Kouichi Kushi, Hajime Sasamoto, and Katsumi Kishino. *Journal of Crystal growth*, 189/190 p109 (1998)
51. **Epitaxial growth of GaN with a high growth rate of 1.4 $\mu\text{m}/\text{h}$ by RF-radical source molecular beam Epitaxy.** Nobuhiko Fujita, Masaki Yoshizawa, Kouichi Kushi, Hajime Sasamoto, Akihiko Kikuchi and Katsumi Kishino. *Journal of Crystal growth*, 189/190 p385 (1998)
52. **The current status of plasma assisted MBE growth of group III-nitrides.** C. T. Foxon and O. H. Hughes. *Journal of Materials Science: Materials in Electronics*. 9 p227 (1998)
53. **Studies of p-GaN grown by MBE on GaAs(1 1 1)B**, C. T. Foxon, T. S. Cheng, N. J. Jeffs, J. Dewsnip, L. Flannery, J. W. Orton, I. Harrison, S. V. Novikov, B. Ya. Ber and Yu. A. Kudriavtsev *Journal of Crystal Growth* 189 p516 (1998)
54. **In situ real-time studies of GaN growth on 6H-SiC(0 0 1) by low-energy electron microscopy (LEEM)** A. Pavlovska, E. Bauer, V. M. Torres, J. L. Edwards, R. B. Doak, I. S. T. Tsong, V. Ramachandran and R. M. Feenstra, *Journal of Crystal Growth* 189-190 p310 (1998)
55. **Ultraviolet and violet GaN light emitting diodes on silicon** S.Guha and N.A.Bojarczuk, *App.Phys.Lett* 72 p415 (1998)
56. **Epitaxial growth of GaN with a high growth rate of 1.4 $\mu\text{m}/\text{h}$ by RF-radical source molecular beam epitaxy** Nobuhiko Fujita, Masaki Yoshizawa, Kouichi Kushi, Hajime Sasamoto, Akihiko Kikuchi and Katsumi Kishino *Journal of Crystal Growth* 189-190 p385 (1998)
57. **Shutter control method for control of Al contents in AlGaIn quasi-ternary compounds grown by RF-MBE** Akihiko Kikuchi, Masaki Yoshizawa, Masashi Mori, Nobuhiko Fujita, Kouichi Kushi, Hajime Sasamoto and Katsumi Kishino *Journal of Crystal Growth* 189-190 p109 (1998)
58. **An XPS study of the effect of nitrogen exposure time and temperature on the GaAs(001) surface using atomic nitrogen** P. Hill, J. Lu, L. Haworth, D. I. Westwood and J. E. Macdonald *Applied Surface Science* 123-124 p126 (1998)
59. **Radio frequency plasma nitridation of c-plane sapphire; influence on properties of GaN grown by molecular beam epitaxy.** Christian Heinlein, Jostein K. Grepstad, Henning Riechert and Robert Averbeck. *J. Mat. Sc. Eng. B58* p270 (1999)
60. **2.6 $\mu\text{m}/\text{h}$ high speed growth of GaN by RF molecular beam epitaxy and improvement of crystal quality by migration enhanced epitaxy** D.Sugihara, A.Kikuchi, K.Kusakabe, S.Nakamura, Y.Toyouura, T.Yamada and K.Kishino *Phys.Stat.Sol* 176 p323 (1999)
61. **Positron studies of MBE-grown gallium nitride** P. Rice-Evans, A. S. Saleh, M. Nathwani, J. W. Taylor and C. T. Foxon *Applied Surface Science* 149 p165 (1999)
62. **The polarity of AlN films grown on Si(1 1 1)** Vadim Lebedev, Bernd Schröter, Gela Kipshidze and Wolfgang Richter *Journal of Crystal Growth* 207 p266 (1999)
63. **Growth of atomically smooth AlN films with a 5:4 coincidence interface on Si(111) by MBE** H. P. D. Schenk, U. Kaiser, G. D. Kipshidze, A. Fissel, J. Kräußlich, H. Hobert^d, J. Schulze and Wo. Richter *Materials Science and Engineering B* 59, p84 (1999)
64. **Ga-metal inclusions in GaN grown on sapphire** A. V. Blant S. V. Novikov, T. S. Cheng, L. B. Flannery, I. Harrison, R. P. Campion, D. Korakakis, E. C. Larkins, Y. Kribes and C. T. Foxon *Journal of Crystal Growth* 203, p349 (1999)
65. **Investigation of two-dimensional growth of AlN(0 0 1) on Si(1 1 1) by plasma-assisted molecular beam epitaxy** H. P. D. Schenk, G. D. Kipshidze, U. Kaiser, A. Fissel, J. Kräußlich, J. Schulze and Wo. Richter *Journal of Crystal Growth* 200 p45 (1999)
66. **Admittance spectroscopy of Mg doped GaN grown by molecular beam epitaxy using RF nitrogen sources** D.J.Kim, D.R.Ryu, K.H.Kim, N.A.Bojarczuk, J.Karasinski and S.Guha, *Jour. Of Korean Phys. Soc.* 34 P S261 (1999)

67. **Selective area metalorganic molecular-beam epitaxy of GaN and the growth of luminescent microcolumns on Si/SiO₂** S.Guha and N.A. Bojarczuk Appl. Phys.Lett. 75 p463 (1999)
68. **Determination of the chemical composition of distorted InGaN/GaN heterostructures from x-ray diffraction data** M.Schuster, P.O.Gervais, B.Jobst, W.Hosler, R.Averbeck, H.Riechert, A.Iberl and S.Stommer, J.Phys.D: Appl.Phys 32 p A56 (1999)
69. **Quantitative model for the MBE-growth of ternary nitrides** R.Averbeck and H.Riechert, Phys.Stat.Sol (a) 176 p301 (1999)
70. **Two-dimensional electron gases induced by spontaneous and piezoelectric polarization charges in N- and Ga-face AlGaIn/GaN heterostructures** O.Ambacher, J.Smart, J.R.Shealy, N.G.Weimann, K.Chu, M.Murphy, R.Dimitrov, L.Wittmer, M.Stutzmann, W.Rieger and J.Hilsenbeck, Journal of Appl. Phys. 85 p3222 (1999)
71. **EXAFS studies of Mg doped InN grown on Al₂O₃** A. V. Blant, T. S. Cheng, N. J. Jeffs, L. B. Flanner, I. Harrison, J. F. W. Mosselmanns, A. D. Smith and C. T. Foxon Materials Science and Engineering B 59 p218 (1999)
72. **Optical characterisation of interface properties for hexagonal GaN grown by MBE on GaAs** S.Shokhovets, R. Goldhahn, G. Gobsch, T. S. Cheng and C. T. Foxon Materials Science and Engineering B 59 p69 (1999)
73. **Raman spectroscopy of disorder effects in Al_xGa_{1-x}N solid solutions** Valery Y. Davydov, Igor N. Goncharuk, Marina V. Baidakova, Alexander N. Smirnov, Arsen V. Subashiev, Jochen Aderhold, Jens Stemmer, Thomas Rotter, Dirk Uffmann and Olga Semchinova Materials Science and Engineering B 59 p222 (1999)
74. **The initiation of GaN growth by molecular beam epitaxy on GaN composite substrates** T. S. Cheng S. V. Novikov, V. B. Lebedev, R. P. Campion, N. J. Jeffs, Yu. V. Melnik, D. V. Tsvetkov, S. I. Stepanov, A. E. Cherenkov, V. A. Dmitriev, D. Korakakis, O. H. Hughes and C. T. Foxon Journal of Crystal Growth 197 p12 (1999)
75. **Gallium-induced surface reconstruction patterns of GaN grown by molecular beam epitaxy** C. T. Foxon, T. S. Cheng, S. V. Novikov, N. J. Jeffs, O. H. Hughes, Yu. V. Melnik, A. E. Nikolaev and V. A. Dmitriev Surface Science 421 p377 (1999)
76. **Controllable cubic and hexagonal GaN growth on GaAs(0 0 1) substrates by molecular beam epitaxy** H. Chen, Z. Q. Li, H. F. Liu, L. Wan, M. H. Zhang, Q. Huang^a, J. M. Zhou, Y. Luo, Y. J. Han, K. Tao and N. Yang Journal of Crystal Growth 210 p811 (2000)
77. **MBE growth and X-ray study of high-quality cubic-GaN on GaAs(0 0 1)** Z. Q. Li, H. Chen, H. F. Liu, J. H. Li, L. Wan, S. Liu, Q. Huang and J. M. Zhou Journal of Crystal Growth 208 p786 (2000)
78. **Direct MBE growth of GaN on GaAs substrates for integrated short wavelength emitters** A.Georakilas, K.Tsagaraki, E.Makarona, C.Constantinidis, M.Adroulidaki, M.Kayambaki, E.Aperathitis, N.T. Pelekanos Mater. Sci in Semicon Process. 3 p511 (2000)
79. **Single crystal hexagonal and cubic GaN growth directly on vicinal (001) GaAs substrates by molecular beam epitaxy** K.Amimer, A.Georakilas, K.Tsagaraki M.Adroulidaki, and D.Cengher Appl. Phys.Lett 76 p2580 (2000)
80. **Reflection high-energy electron diffraction intensity oscillations during growth of GaN(0001)A by plasma-assisted molecular beam epitaxy** S. M. Seutter, M. H. Xie, W. K. Zhu, L. X. Zheng, H. S. Wu and S. Y. Tong Surface Science 455 p L71 (2000)
81. **High temperature AlN intermediate layer in GaN grown by molecular beam epitaxy.** J. Stemmer, F. Fedler, H. Klausung, D. Mistele, T. Rotter, O. Semchinova, J. Aderhold, A. M. Sanchez, F. J. Pacheco, S. I. Molina, M. Fehrer, D. Hommel and J. Graul. Journal of Crystal Growth 216 p15 (2000)
82. **Optical quality of GaNAs and GaInNAs and its dependence on RF cell condition in chemical beam epitaxy.** Takeo Kageyama, Tomoyuki Miyamoto, Shigeki Makino, Fumio Koyama and Kenichi Iga. Journal of Crystal Growth 209 350-354 (2000)

83. **Growth of quaternary AlInGaN/GaN heterostructures by plasma-induced molecular beam epitaxy** A. P. Lima C. R. Miskys, U. Karrer, O. Ambacher, A. Wenzel B. Rauschenbach and M. Stutzmann Journal of Crystal Growth 220 p341 (2000)
84. **Structural properties of Al_xGa_{1-x}N grown on sapphire by molecular beam epitaxy** Je Won Kim, Chang-Sik Son, In-Hoon Choi, Young K. Park, Yong Tae Kim, O. Ambacher and M. Stutzmann, Journal of Crystal Growth 208 p37 (2000)
85. **Investigation into the influence of buffer and nitrided layers on the initial stages of GaN growth on InSb (100)** L. Haworth, J. Lu, D. I. Westwood and J. E. Macdonald Applied Surface Science 166 p418 (2000)
86. **Influence of N/Ga-flux ratio on optical properties and surface morphology of GaN grown on sapphire(0001) by MBE** O. Zsebök, J. V. Thordson, Q. X. Zhao and T. G. Andersson Applied Surface Science 166 p423 (2000)
87. **Atomic hydrogen cleaning, nitriding and annealing InSb (100)** L. Haworth, J. Lu, D. I. Westwood and J. E. MacDonald Applied Surface Science 166 p253 (2000)
88. **Nanocrystals at MBE-grown GaN/GaAs(001) interfaces** O. Zsebök, J. V. Thordson, L. Ilver and T. G. Andersson Applied Surface Science 166 p317 (2000)
89. **Thermal removal of oxide and carbide from 6H-SiC surfaces before molecular beam epitaxial growth of GaN** Z. P. Guan, A. L. Cai, H. Porter, J. Cabalu, S. Huang and R. E. Giedd Applied Surface Science 165 p203 (2000)
90. **Influence of oxygen and methane plasma on the electrical properties of undoped AlGaIn/GaN heterostructures for high power transistors** R. Dimitrov, V. Tilak, W. Yeo, B. Green, H. Kim, J. Smart, E. Chumbes, J. R. Shealy, W. Schaff, L. F. Eastman, C. Miskys, O. Ambacher and M. Stutzmann Solid-State Electronics 44 p1361 (2000)
91. **Arsenic-doped GaN grown by molecular beam epitaxy** C.T.Foxon, S.V.Novikov, T.S.Cheng, C.S.Davis, R.P.Campion, A.J.Winser and I.Harrison, Journal of Crystal Growth 219 p327 (2000)
92. **Microstructure of Fe-N thin films prepared using an atomic nitrogen beam.** N. D. Telling, G. A. Jones, C. A. Faunce, P. J. Grundy, H. J. Blythe and D. E. Joyce. J. Vac. Sci. Technol. A 19(2) p405 (2001)
93. **Carrier relaxation dynamics for As defects in GaN** B.Gil, A.Morel, T.Taliercio, P.Lefebvre, C.T.Foxon, I.Harrison, A.J.Winser and S.V.Novikov Appl.Phys.Lett 79 p69 (2001)
94. **A study of the mechanisms responsible for blue emission from arsenic-doped gallium nitride** S.V.Novikov, A.J.Winser, I.Harrison, C.S.Davis and C.T. Foxon, Semicon.Sci.Technol 16 p103 (2001)
95. **A structural study of phase transitions within GaN layers grown by low-temperature molecular beam epitaxy** S. Marlafeka, N. Bock, T. S. Cheng, S. V. Novikov, A. J. Winser, I. Harrison, C. T. Foxon and P. D. Brown, Journal of Crystal Growth 230 p415 (2001)
96. **Blue emission from arsenic doped gallium nitride** A. J. Winser, I. Harrison, S. V. Novikov, C. S. Davis, R. Campion, T. S. Cheng and C. T. Foxon Journal of Crystal Growth Volume 230 p527 (2001)
97. **Hexagonal AlN films grown on nominal and off-axis Si(0 0 1) substrates** V. Lebedev, J. Jinschek, J. Kräußlich, U. Kaiser, B. Schröter and W. Richter Journal of Crystal Growth Volume 230 p426 (2001)
98. **Surface reconstruction patterns of AlN grown by molecular beam epitaxy on sapphire** C. S. Davis, S. V. Novikov, T. S. Cheng, R. P. Campion and C. T. Foxon, Journal of Crystal Growth 266 p203 (2001)
99. **Correlation of the structural and optical properties of GaN grown on vicinal (0 0 1) GaAs substrates with the plasma-assisted MBE growth conditions** A. Georgakilas, K. Amimer, P. Tzanetakis, Z. Hatzopoulos, M. Cengher, B. Pecz, Zs. Czigany L. Toth, M. V. Baidakova, A. V. Sakharov and V. Yu. Davydov Journal of Crystal Growth 227-228 p410 (2001)

100. **Study of the correlation between GaN material properties and the growth conditions of radio frequency plasma-assisted molecular beam epitaxy** K. Amimer, A. Georgakilas, M. Androulidaki, K. Tsagaraki, M. Pavelescu, S. Mikroulis, G. Constantinidi, J. Arbiol, F. Peiro, A. Cornet, M. Calamiotou, J. Kuzmik and V. Y. Davydov, *Materials Science and Engineering B* 80 p304 (2001)
101. **InN thin films grown by metalorganic molecular beam epitaxy on sapphire substrates** J. Aderhold, V. Yu. Davydov, F. Fedler, H. Klausing, D. Mistele, T. Rotter, O. Semchinova, J. Stemmer and J. Graul *Journal of Crystal Growth* 222 p701 (2001)
102. **X-ray studies of As-doped GaN grown by plasma-assisted molecular beam epitaxy** T. Li, C. R. Staddon, S. V. Novikov, P. F. Fewster, A. Widdowson, N. L. Andrew, P. Kidd, I. Harrison, A. Winsor, Y. Liao and C. T. Foxon, *Journal of Crystal Growth* 235 p103 (2002)
103. **RF plasma investigations for plasma-assisted MBE growth of (Ga,In)(As,N) materials** H. Carrère, A. Arnoult, A. Ricard and E. Bedel-Pereira, *Journal of Crystal Growth* 243 p295 (2002)
104. **Intersubband transition in (GaN)_m/(AlN)_n superlattices in the wavelength range 1.08 to 1.61 μm** K. Kishino, A. Kikuchi, H. Kanazawa and T. Tachibana *Appl. Phys. Lett.* 81 p1234 (2002)
105. **Improved molecular beam epitaxy for fabricating AlGaIn/GaN heterojunction devices** K. Kishino and A. Kikuchi *Phys. Stat. Sol. (a)* 190 p23 (2002)
106. **Structural characterisation of Al grown on group III-nitride layers and sapphire by molecular beam epitaxy** P. D. Brown, M. Fay, N. Bock, S. Marlafecka, T. S. Cheng, S. V. Novikov, C. S. Davis, R. P. Campion and C. T. Foxon, *Journal of Crystal Growth* 234 p384 (2002)
107. **Growth of high-quality InN using low-temperature intermediate layers by RF-MBE** Y. Saito, T. Yamaguchi, H. Kanazawa, K. Kano, T. Araki, Y. Nanishi, N. Teraguchi and A. Suzuki *Journal of Crystal Growth* 237 p1017 (2002)
108. **Origin of the radiative emission in blue–green light emitting diodes based on GaN/InGaIn heterostructures** J. R. Leite, *Microelectronics Journal* 33 p323 (2002)
109. **Correlation between transport, optical and structural properties in AlGaIn/GaN heterostructures** A. Jiménez, E. Calleja, E. Muñoz, M. Varela, C. Ballesteros, U. Jahn, K. Ploog, F. Omnés and P. Gibart *Materials Science and Engineering B* 93 p64 (2002)
110. **Plasma-assisted MBE growth of group-III nitrides: from basics to device applications** M. A. Sánchez-García, J. L. Pau, F. Naranjo, A. Jiménez, S. Fernández, J. Ristic, F. Calle, E. Calleja and E. Muñoz *Materials Science and Engineering B* 93 p189 (2002)
111. **Near band-edge optical properties of cubic GaN** J. R. L. Fernandez, O. C. Noriega, J. A. N. T. Soares, F. Cerdeira, E. A. Meneses, J. R. Leite, D. J. As, D. Schikora and K. Lischka, *Solid State Communications* 125 p205 (2003)
112. **Photoreflectance studies of optical transitions in cubic GaN grown on GaAs(0 0 1) substrates** O. C. Noriega, A. Tabata, J. A. N. T. Soares, S. C. P. Rodrigues, J. R. Leite, E. Ribeiro, J. R. L. Fernandez, E. A. Meneses, F. Cerdeira, D. J. As, D. Schikora and K. Lischka, *Journal of Crystal Growth* 252 p208 (2003)
113. **Improvement of cubic GaN film crystal quality by use of an AlN/GaN ordered alloy on GaAs (1 0 0) by plasma assisted molecular beam epitaxy** Ryuhei Kimura, Atsushi Shigemori, Junichi Shike, Koichi Ishida and Kiyoshi Takahashi, *Journal of Crystal Growth* 251 p455 (2003)
114. **The effect of V:III ratio on the growth of InN nanostructures by molecular beam epitaxy** R. A. Oliver, C. Nörenberg, M. G. Martin, M. R. Castell, L. Allers and G. A. D. Briggs, *Surface Science* 532-535 p806 (2003)
115. **Arsenic incorporation in GaN during growth by molecular beam epitaxy** C. T. Foxon, S. V. Novikov, T. Li, R. P. Campion, A. J. Winsor, I. Harrison, M. J. Kappers and C. J. Humphreys *Journal of Crystal Growth* 251 p510 (2003)

Dilute Nitrides

116. **Gas-source molecular beam epitaxy of GaN_xAs_{1-x} using a N radical as the N source.** M.Kondow, K.Uomi, K. Hosomi and T. Mozume, Jpn. J. Appl. Phys. 33 p L1056 (1994)
117. **Extremely large N content (up to 10%) in GaNAs grown by gas-source molecular beam epitaxy.** M. Kondow, K. Uomi, T. Kitatani, S. Watahiki and Y. Yazawa. Journal of crystal growth. 164 p175 (1996)
118. **Room-temperature continuous-wave operation of GalnNAs/GaAs laser diode,** M.Kondow, S.Natatsuka, T.Kitatani, Y.Yazawa and M.Okai, Electronics Letters 32 p2244 (1996)
119. **The effect of N incorporation in II-Vs: optical properties of InAsPN/GalnP multiple quantum wells.** X. B. Mei and C. W. Tu. Presented at Nitride semiconductors symposium 1997 Fall MRS meeting, Boston USA (1997)
120. **N incorporation in GaN_xP_{1-x} and InN_xP_{1-x} using a RF plasma source** W.G.Bi and C.W.Tu, Journal of Crystal Growth 175-176 p145 (1997)
121. **Chemical beam epitaxy growth and characterisation of GaNAs/GaAs,** K. Takeuchi, T.Miyamoto, T.Kageyama, F.Koyama and K. Iga Jpn. J. Appl. Phys 37 p1603 (1998)
122. **Properties of molecular-beam epitaxy-grown GaNAs from optical spectroscopy,** G.Pozina, I.Ivanov, B.Monemar, J.V.Thordson and T.G.Andersson, Journ. Of Appl.Phys 84 p3830 (1998)
123. **Quantum dot-like behaviour of GalnNAs/GaAs quantum wells grown by gas-source molecular-beam epitaxy.** H. P. Xin, K. L. Kavanagh, Z. Q. Zhu and C. W. Tu. J. Vac. Sci. Technol. B 17(4) p1649 (1999)
124. **1.29µm GalnNAs multiple quantum-well ridge-waveguide laser diodes with improved performance,** B.Borchet, A.Egorov, S.Illek, M.Komainda and H.Riechert, Electronics Letters 35 p2204 (1999)
125. **High power CW operation of GalnNAs lasers at 1.3µm,** A.Egorov, D.Bernklau, D.Livshits V.Ustinov, Z Alferov and H.Riechert, Electronics Letters 35 p1643 (1999)
126. **Chemical beam epitaxy of GalnNAs/GaAs quantum wells and its optical absorption property** Tomoyuki Miyamoto, Kanji Takeuchi, Takeo Kageyama, Fumio Koyama and Kenichi Iga, Journal of Crystal Growth 197 p67 (1999)
127. **Optical quality of GaNAs and GalnNAs and its dependence on RF cell condition in chemical beam Epitaxy.** Takeo Kageyama, Tomoyuki Miyamoto, Shigeki Makino, Fumio Koyama and Kenichi Iga. Journal of Crystal Growth 209 p350 (2000)
128. **Gas-source molecular beam epitaxial growth and thermal annealing of GalnAs/GaAs quantum wells,** H. P. Xin, K. L. Kavanagh and C. W. Tu. Journal of Crystal Growth 208 p145 (2000)
129. **Molecular beam epitaxial growth of GaAs_{1-x}N_x with dispersive nitrogen source,** S.Z.Wang, S.F.Yoon, T.K.Ng, W.K.Loke, W.J.Fan, Journal of Crystal Growth 242 p87 (2002)
130. **Band structure and optical gain in GalnAsN quantum wells** H.Carrere, A.Arnoult, X.Marie, T.Amand, E.Bedel-Pereira, R.J.Potter and N.Balkan, Physica E 17 p245 (2003)
131. **GaAsN and GalnAsN/GaAs quantum well grown on (111) substrates: growth conditions and optical properties** S.Blanc, A.Arnoult, H.Carrere and C.Fontaine, Physica E, 17 p252 (2003)
132. **A comparison of MBE-a and MOCVD-grown GalnNAs** A.J.Ptak, S.W.Johnston, S.Kurtz, D.J.Friedman and W.K.Metzger, Journal of Crystal Growth, 251 p392 (2003)
133. **Interest of the (111) orientation for GaAsN and GalnAsN/GaAs** S.Blanc, A.Arnoult, H.Carrere and C.Fontaine, Solid State Electronics 47 p395 (2003)
134. **Nitrogen plasma study for plasma-assisted MBE growth of 1.3µm laser diodes** H.Carrere, A.Arnoult, A.Ricard, X.Marie, T.Amand, E.Bedel-Pereira Solid State Electronics p419 (2003)

Nitrogen Doping

135. ***P-type ZnSe by nitrogen atom beam doping during molecular beam epitaxial growth.*** R Park, M Troffer, C Rouleau, J DePuydt & M Hasse. Appl Phys Lett **57** (20), p2127 (1990)
136. ***Characteristics of p-type ZnSe layers grown by molecular beam epitaxy with radical doping.*** K Ohkawa, T Karasawa & T Mitsuyu. Jap J Appl Phys **30** (2a), p152 (1991)
137. ***Doping of nitrogen acceptors into ZnSe using a radical beam during MBE growth.*** K Ohkawa, T Karasawa & T Mitsuyu. J Crystal Growth **111**, p797 (1991)
138. ***Heavily Doped p-ZnSe:N grown by molecular beam epitaxy.*** J Qiu, J DePuydt, H Cheng & M Haase. Appl Phys Lett **59** (23), p2992 (1991)
139. ***Blue electroluminescence from ZnSe p-n junction light-emitting diodes.*** K Ohkawa, A Ueno & T Mitsuyu. Jap J Appl Phys **30** (12b), p3873 (1991)
140. ***Blue/green injection lasers and light emitting diodes.*** W Xie, D Grillo, R Gunshor, M Kobayashi, G Hua, N Otsuka, H Jeon, J Ding & A Nurmikko. J Vac Sci Tech B **10** (2), p921 (1992)
141. ***Low-resistivity p-type ZnSe:N grown by molecular beam epitaxy using a nitrogen free-radical source.*** R Park. J Vac Sci Tech A **10** (4), p701 (1992)
142. ***Heavy p-doping of ZnTe by molecular beam epitaxy using a nitrogen plasma source.*** J Han, T Stavrinides, M Kobayashi, R Gunshor, M Hagerott & V Nurmikko. Appl Phys Lett **62** (8), p840 (1993)
143. ***Acceptor concentration control of p-ZnSe using nitrogen and helium mixed gas plasma.*** H Tosaka, T Nagatake, T Yoshida, M Kobayashi & A Yoshikawa. Jap J Appl Phys **32** (Pt212a), p1722 (1993)
144. ***Electrical characterisation of p-type ZnSe:N and Zn_{1-x}Mg_xSySe_{1-y}:N thin films.*** P M Mensz, S Herko, K W Haberen, J Gaines and C Ponzoni. Appl Phys Lett **63** (20), p2060 (1993)
145. ***Effect of N doping on the structural properties of ZnSe epitaxial layers grown by molecular beam epitaxy.*** J. Petruzzello, J. Gaines, P. van der Sluis, D. Olego and C. Ponzoni. Appl. Phys. Lett. **62** (13) 1496 (1993)
146. ***Structural properties of nitrogen-doped ZnSe epitaxial layers grown by MBE.*** J. Petruzzello, J. Gaines, P. van der Sluis, D. Olego, T. Marshall, and C. Ponzoni. Journal of electronic materials. **22** (5) p453 (1993)
147. ***Atomic nitrogen production in nitrogen-plasma sources used for the growth of ZnSe:N and related alloys by molecular-beam epitaxy.*** R.P. Vaudo, J.W. Cook, Jr & J.F. Schetzina. J. Crystal Growth **138**, p430 (1994)
148. ***Enhancement of nitrogen incorporation in ZnSe grown on misorientated GaAs substrates by molecular beam epitaxy.*** Nishikawa Y, Ishiakwa M, Saito S and Hatakoshi G. Jpn J Appl Phys **33**, p L361 (1994)
149. ***Active-nitrogen doped p-type ZnSe grown by gas source molecular beam epitaxy for blue light emitting devices.*** M Imaizumi, Y Endoh, K Ohtsuka, T Isu and M Nunoshita. Jpn J Apply Phys **32** p1725 (1994)
150. ***Some doping results in ZnSe grown by molecular beam epitaxy*** L.K. Li and W.I. Wang, J. M. Gaines, J. Petruzzello and T. Marshall. J. Vac. Sci. Technol. B **12**(2), p1197 (1994).
151. ***Observations on the limits to p-type doping in ZnSe.*** Y. Fan, J. Han, L. He and R. L. Gunshor. Appl. Phys. Lett. **65**, p1001 (1994)
152. ***Pressure dependence of the photoluminescence spectra of nitrogen-doped ZnSe: Evidence of compensating deep donors.*** A. L. Chen, W. Walukiewicz and E. Haller. Appl. Phys. Lett. **65** (1994).
153. ***P- and N- type doping of ZnSe: effects of hydrogen incorporation.*** P.A. Fischer, E. Ho, J.L. House, G.S. Petrich, L.A. Kolodzieski, J. Walker, N. M. Johnson. Proceedings, Eighth International Conference on Molecular Beam Epitaxy, Osaka, Japan (1994)

154. **Characterisation of N-doped MgZnSSe compound system grown on intentionally misoriented GaAs substrates by MBE.** Y. Ichimura, K. Kishino, M. Satake, M. Kuramoto and A. Yoshida. Proceedings, Eighth International Conference on Molecular Beam Epitaxy, Osaka, Japan (1994)
155. **Growth and characterisation of N-doped ZnS_xSe_{1-x} (0<x<0.3) by MBE,** N.Teraguchi, S.Hirata, Y.Tomomura, H.Mouri, A.Suzuki and H.Takiguchi, Proceedings, Eighth International Conference on Molecular Beam Epitaxy, Osaka, Japan (1994)
156. **Structural and Electrical properties of ZnSe laser diodes optimised by TEM, RHEED, X-ray diffraction and C-V profiling.** T. Behr, D. Hommel, H. Cerva, J. J. Nürnbergger, V. Beyersdorfer and G. Landwehr. Proceedings, Eighth International Conference on Molecular Beam Epitaxy, Osaka, Japan (1994)
157. **High -brightness light-emitting diodes grown by molecular beam epitaxy on ZnSe substrates,** D. B. Eason, Z. Yu, W. C. Hughes, C. Boney, J. W. Cook,Jr and J. F. Schetzina. J. Vac. Sci. Technol. B. **13(4)** p1566 (1995)
158. **p-Type doping of ZnSe; on the properties of nitrogen in ZnSe:N.** E. Kurtz, S. Einfeldt, J. Nürnbergger, S. Zerlauth, D. Hommel and G. Landwehr. Phys. Stat. Sol. (b) **187**, p393 (1995)
159. **Hydrogen passivation in nitrogen and chlorine-doped ZnSe films grown by gas source molecular beam epitaxy.** E. Ho, P.A. Fisher, J. L. House, G. S. Petrich, L. A. Kolodziejcki, J. Walker and N. M. Johnson. Appl. Phys. Lett. **66** (9) p1062 (1995)
160. **Status of II-VI molecular-beam epitaxy technology,** O.K.Wu, R.D.Rajavel and J.E.Jensen, Materials Chemistry and Physics 43 p103 (1996)
161. **Novel results on compensation processes in ZnSe:N,** E.Kurtz, J.Nurnberger, B.Jobst, H.Baumann, M.Kuttler, S.Einfeldt, D.Hommel, H.Landwehr, K.Bethge, D.Bimber, Journal of Crystal Growth 159 p289 (1996)
162. **Defect reduction in ZnSe grown by molecular beam epitaxy on GaAs substrates cleaned using atomic hydrogen.** Zhonghai Yu, S.L. Buczkowski, N.C. Giles and T.H. Myers. Appl. Phys. Lett. **69** (1) (1996)
163. **Compensating defects in heavily nitrogen-doped zinc selenide: a photoluminescence study.** M. Moldovan, S. D. Setzler, T. H. Myers, L. E. Halliburton and N. C. Giles. Appl. Phys. Lett. **70** (13) p1724 (1997)
164. **p-Type doping of beryllium-chalcogenides.** H.-J. Lugauer, F. Fischer, T. Litz, A. Waag, U. Zehnder, W. Ossau, T. Gerhard, H. Ress, G. Landwehr, C. Becker, R. Kruse and J. Geurts. Materials Science and Engineering B 43 p88 (1997)
165. **p-Type doping of beryllium chalcogenides grown by molecular beam epitaxy** H.-J. Lugauer, F. Fischer, T. Litz, A. Waag, U. Zehnder, W. Ossau, T. Gerhard, H. Ress, G. Landwehr, C. Becker, R. Kruse and J. Geurts. Journal of Crystal Growth 15 p619 (1997)
166. **Molecular beam epitaxy of p-type ZnSSe using a nitric oxide plasma source.** P. Uusimaa, K. Rakennus, A. Salokatve, M. Pessa and J. Likonen. J. Vac. Sci. Technol. A **15(4)** (1997)
167. **MBE growth of II-VI semiconductors for short wavelength lasers.** M. D. Pashley, J. Petruzzello, C. Ponzoni-Wakeman and B. Rossi. IX European workshop on MBE, Oxford, UK (1997)
168. **Hole trap generation by thermal treatment of nitrogen doped p-type ZnSe on GaAs characterized by deep level transient spectroscopy.** K. Hellig, G Prösch, M. Behringer, M. Fehrer, B. Beyer, H. Burghardt, D. Hommel and D. R. T. Zahn, Appl. Phys. Lett. **71** (15) p2187 (1997)
169. **Optimized ZnSe:N/ZnTe:N contact structure of ZnSe-based II-VI laser diodes.** Satoru Kijima, Hiroyuki Okuyama, Yumi Sanaka, Takashi Koboyashi, Shigetaka Tomiya and Akira Ishibashi (Sony Research centre). Applied Physics letters **73** (2), p235 (1998)
170. **Lasing Characteristics of low threshold ZnSe-based blue/green laser diodes grown on conductive ZnSe substrates.** K. Katayama, H. Yao, F. Nakanishi, H. Doi, A. Saegusa, N. Okuda, T. Yamada, H. Matsubara, M. Irikura, T. Matsuoka, T. Takebe, S. Nishine and T. Shirakawa. Applied Physics Letters, **73** (1), p102 (1998)

171. **The nitrogen-related shallow donor in ZnSe: N epitaxial layers**, E.Tournie, C.Morhain, G.Neu and J.-P.Faurie, Journal of Crystal Growth 184-185 p520 (1998)
172. **Influence of p-type doping on the degradation of ZnSe laser diodes** D.Albert, J.Nurnberger, V.Hock, M.Ehinger, W.Faschinger and G.Landwehr Applied Physics Letters, 74 p1957 (1999)
173. **P-type doping of ZnSe and related materials controlled by diluting nitrogen in an inert gas** E.Tournie, P.Brunet and J.-P.Faurie, Journal of Crystal Growth 201-202 p938 (1999)
174. **The influence of magnesium on p-type doping and optoelectronic properties of Zn_{1-x}Mg_xSe-based heterostructures** B.Vogele, C.Morhain, B.Urbaszek, S.A.Telfer, K.A.Prior and B.C.Cavenett, Journal of Crystal Growth 201-202 p950 (1999)
175. **Shallow donors in ultrathin nitrogen-doped ZnSe layers – a novel or a disregarded mechanism in II-VI device structures?** S.Strauf, P.Michler, J.Gutowski, M.Klude and D.Hommel, Journal of Crystal Growth 214-215 p497 (2000)
176. **Spin-valve magnetization reversal obtained by N-doping in Fe/insulator/Fe trilayers** M.T.Georgieva, N.D.Telling, G.A.Jones, P.J.Grundy, T.P.A.Hase and B.K.Tanner, J.Phys:Condens. Matter 15 p617 (2003)

Nitrogen surface treatment

177. ***Plasma preconditioning of sapphire substrate for GaN epitaxy.*** C. Heinlein, J. Grepstad, H. Riechert and R. Averbeck. Materials Science and Engineering B 43 p253 (1997)
178. ***Preconditioning of c-plane sapphire for GaN epitaxy by radio frequency plasma nitridation.*** C. Heinlein, J. Grepstad, T. Berge and H. Riechert. Appl. Phys. Lett **71**(3) p341 (1997)
179. ***the (3x3) reconstruction and its evolution during the nitridation of GaAs(001)*** J.Lu, D.I.Westwood, L.Haworth, P.Hill and J.E.Macdonald, Thin Solid Films 343-344 p567 (1999)
180. ***ZnSe epitaxial films grown by MBE on nitrogen treated Si(111) substrates*** V.H. Mendez-Garcia, M.Lopez-Lopez and I.Hernandez-Calderon, Superficies y Vacio 8 p46 (1999)
181. ***Two-dimensional growth mode promotion of ZnSe on Si(111) by using a nitrogen substrate surface treatment*** V.H. Mendez-Garcia and M.Lopez-Lopez Journal of Crystal Growth 201-202 p518 (1999)
182. ***Improvement in the crystal quality of ZnSe films on Si(111) with a nitrogen surface treatment*** V.H. Mendez-Garcia, A.Perez Centeno, M.Lopez-Lopez, M.Tamura, K.Momose, K.Ojima and H.Yonezu, Thin Solid Films 373 p33 (2000)
183. ***Atomic hydrogen cleaning, nitriding and annealing of InSb*** L.Haworth, J.Lu, D.I.Westwood and J.E.MacDonald, Applied Surface Science 166 p253 (2000)

Oxides

184. **Oxidation of cold copper films with oxygen radicals** R Clampitt & P Hanley. Supercond Sci Technol 1, p5 (1988)
185. **In-situ MBE growth of epitaxial CuO films with a source of activated oxygen.** J-P Locquet. J Less-Common Metals 164 & 165, p300 (1990)
186. **Characterisation of a radio frequency plasma source for molecular beam epitaxial growth of high-Tc superconductor films.** J-P Locquet & E Mächler. J Vac Sci Tech A 10 (5), p3100 (1992)
187. **Preparation of YBa₂Cu₃O_{7-x} films and YBa₂Cu₃O_{7-x}/Y₂O₃ multilayers using coevaporation and atomic oxygen.** J Hudner, M Östling, H Ohlsén, L Stolt, P Nordblad, M Ottosson, J-C Villegier, H Moriceau, F Weiss & O Thomas. Submitted to Appl Phys Lett 11 p8 (1992)
188. **In-situ preparation of YBaCuO thin films using mass-spectrometer rate control and atomic oxygen.** H Ohlsén, M Ottosson, J Hudner, M Ostling, L Stolt, P Nordblad, J-C Villegier, H Moriceau, F Weiss & O Thomas. Mat Res Soc Symp Proc 275, p299 (1992)
189. **Structural study of MBE-grown DyBa₂Cu₃O₇/Dy₂O₃ films on SrTiO₃.** A Catana & J-P Locquet. Appl Surf Sci 65-66, p192 (1993)
190. **Block by block deposition: A new growth method for complex oxide films.** J P Locquet, A Catana, E Mächler, Ch Berber and J g Bednorz. IBM Research Report RZ 2524 (#82832) (1993)
191. **The characterisation of thin films of MBE grown La_{2-x}Sr_xCuO_{4±d} by transmission electron microscopy.** E J Williams, J P Locquet, E Mächler, Y Jaccard, A Cretton, RF Broom, C Gerber, T Schneider, P Martinoli and O Fischer. Proc Electron Microscopy and analysis group conf. "EMAG'93", Liverpool, UK Sept. 14-17, (1993)
192. **Electrochemical oxidation of La₂CuO₄ thin films grown by molecular beam epitaxy.** J P Locquet, C Gerber, A Cretton, Y Jaccard, E William and E Mächler. Appl Phys A 57, p211 (1993)
193. **The origin of Cu-rich precipitate formation on superconducting films: A competition between nucleation, oxidation and growth kinetics.** J P Locquet, C Gerber and E Mächler. Appl Phys Lett, 63, p1426 (1993)
194. **Domain growth of Dy₂O₃ buffer layers on SrTiO₃.** A Catana and J P Locquet. J Mater Res 8 (6), p1373 (1993).
195. **Conductance noise and percolation in YBa₂Cu₃O₇ thin films.** L Kiss, T Larsson, P Svedlindh, L Lundgren, H Ohlsén, M Ottosson, J Hudner & L Stolt. Physica B.
196. **Properties of yttrium oxide thin films on silicon (100) prepared by evaporation of yttrium in atomic oxygen.** J Hudner, H Ohlsén & E Fredriksson. MRS Proceedings Spring 94. Epitaxial Oxide Heterostructures symposium (1994)
197. **Effect of oxygen radicals for epitaxial growth of Al₂O₃ on Si.** K Hayama, M Ishida & T Nakamura. Jap J Appl Phys 33, p496 (1994)
198. **Tantalum oxide films on silicon grown by tantalum evaporation in atomic oxygen** J.Hudner, P-E.Hellberg, D.Kusche and H.Ohlsen, Thin Solid Films 281 p415 (1996)
199. **Electron spectroscopy study of the Cu/SrTiO₃(100) interface** T.Conard, A-C.Rousseau, L.M.Yu, J.Ghijsen, R.Sporcken, R.Caudano and R.L.Johnson Surface Science 359 p82 (1996)
200. **Photoemission study of the Bi/CuO interface** T.Conard, A-C.Rousseau, L.M.Yu, J.Ghijsen, R.Sporcken, R.Caudano and R.L.Johnson Surface Science 369 p177 (1996)
201. **Visible light emission from MBD-grown Si/SiO₂ superlattices** S.V.Novikov, J.Sinkkonen, O.Kipela and S.V.Gastev Journal of Crystal Growth 175-176 p514 (1997)

202. **Heteroepitaxial growth of Al_2O_3 film on Si using dimethylethylamine-alane and O_2**
K.Hayama, T.Togun and M.Ishida, Journal of Crystal Growth 179 p 433 (1997)
203. **In situ growth of evaporated TiO_2 thin films using oxygen radical: Effect of deposition temperature.** J. V. Grahn, M. Linder and E. Fredriksson. J. Vac. Sci. Technol. A 16(4) p2495 (1998)
204. **Effect of growth temperature on the properties of evaporated tantalum pentoxide thin films on silicon deposited using oxygen radicals.** J. V. Grahn, P. -E. Hellberg and E. Ollson. J. Appl. Phys. 84 (3), p1632 (1998)
205. **Experimental and theoretical studies of the low-temperature growth of chromia and alumina** D.E.Ashenford, F.Long, W.E.Hagston, B.Lunn and A.Matthews Surface Coating and Technology 116-119 p699 (1999)
206. **On light-emitting mechanism in Si/SiO_2 superlattices grown by molecular beam deposition,** S.V.Novikov, O.Kipela, J.Sinkkonen and L.Khriachtchev, Microelectronic Engineering 51 p505 (2000)
207. **Effect of sodium and oxygen doping on the conductivity of $CuInS_2$ films** R.Scheer, I.Luck, M.Kanis, R.Kurps and D.Kruger, Thin Solid Films 361-362 p468 (2000)
208. **Development of high dielectric constant epitaxial oxides on silicon by molecular beam epitaxy,** R.Droopad, Z.Yu, J.Ramdani, L.Hilt, J.Curlless, C.Overgaard, J.L.Edwards Jr, J.Finder, K.Eisenbeiser, W.Ooms Materials Science and Engineering B 87 p292 (2001)
209. **MBE Lanthanum-based high-k gate dielectrics as candidates for SiO_2 gate oxide replacement** G.Velliantis, G.Apostolopoulos, G.Mavrou, A.Dimoulas, J.C.Hooker, T.Conard, M.Butcher Proceedings of the EMRS meeting, Stasbourg (2003)

Hydrogen Cleaning

210. **Metalorganic molecular beam epitaxy of GaAs using hydrogen radical beam.** A Watanabe, M Hata & T Isu. J Crystal Growth **111**, p554 (1991)
211. **Surface Interactions of thermal beams of atomic hydrogen** R.Clampitt and C.Sofield, Presented at UCPSS, Leuven (1992)
212. **GaAs substrate cleaning for epitaxy using a remotely generated atomic hydrogen beam.** C Rouleau & R Park. J Appl Phys **73** (9), p4610 (1993)
213. **In-Situ native oxide removal from AlGaInAs surfaces by hydrogen radical treatment for molecular beam epitaxy regrowth.** A. Hase, R Gibbs, I Griebenow and H Künzel. Appl.Phys.Lett 65 p1406 (1994)
214. **In-situ Al_{0.24}Ga_{0.24}In_{0.52}As surface cleaning procedure using hydrogen radicals for MBE re-growth.** H. Kunzel, R. Bochnia, J Böttcher, P. Harde, A. Hase and U. Griebenow. Journal of Crystal Growth 150 p18 (1995)
215. **In-Situ low temperature cleaning of silicon surfaces using hydrogen atoms.** A.Crossley, C.J.Sofield, S.Sugden, R.Clampitt and C.Bradley, Vacuum 46 p667 (1995)
216. **Hydrogen radical surface cleaning of GaAs for MBE re-growth.** T. M. Burke, E. H. Linfield, M. A. Quierin, D. A. Ritchie and M. Pepper. Proceedings Ninth international conference on molecular beam epitaxy. Malibu, USA (1996)
217. **MBE regrowth on AlGaInAs DFB Gratings using in-situ Hydrogen radical cleaning,** H. Künzel, J. Böttcher, A. Hase, H.-J. Hensel, K. Janiak, A. Paraskevopoulos and G. Urmann. Proceedings Ninth international conference on molecular beam epitaxy. Malibu, USA (1996)
218. **Surface decontamination of patterned GaAs substrates for molecular beam epitaxy regrowth using a hydrogen radical source.** T. M. Burke, M. A. Quierin, M. P. Grimshaw, D. A. Ritchie, M. Pepper and J. H. Burroughes. J. Vac. Sci. Technol. B **15**(2) p325 (1997)
219. **Surface preparation of ZnSe substrates for MBE growth of II-VI emitters.** W.C.Hughes, C.Boney, M.A.L.Johnson, J.F.Schetzina and J.W.Jr.Cook, Journal of Crystal Growth 15-176 p546 (1997)
220. **Plasma preconditioning of sapphire substrate for GaN epitaxy.** C. Heinlein, J. Grepstad, H. Riechert and R. Averbeck. Materials Science and Engineering B **43** p253 (1997)
221. **Optimised processing for differentially molecular beam epitaxy-grown SiGe devices** G.Lippert, H.J.Osten, K.Blum, R.Sorge, P.Schley, D.Kruger and G.Fischer Thin Solid Films 321 p21 (1998)
222. **Mobility ($10^6 \text{ cm}^2 \text{V}^{-1} \text{s}^{-1}$) of 2DEGs, 30nm from ex situ patterned GaAs re-growth interfaces.** T.M.Burke, D.A.Ritchie, E.H.Linfield, M.P.O'Sullivan, J.H.Burroughes, M.L.Leadbeater, S.N.Holmes, C.E.Norman, A.J.Shields and M.Pepper Materials Science and Engineering B **51** p202 (1998)
223. **Hydrogen radical cleaning and low energy electron stimulated desorption of surface contaminants for MBE growth** T.M.Burke, S.J.Brown, M.P.Smith E.H.Linfield, D.A.Ritchie, M.Pepper K.B.K.Tang, R.E.Palmer and J.H.Burroughes, Applied Surface Science 123-124 p308 (1998)
224. **Homoepitaxial laser diodes grown on conducting and insulating ZnSe substrates** H.Wenisch, M.Fehrer, M.Klude, Journal of Crystal Growth 201-202 p933 (1999)
225. **Atomic hydrogen cleaning, nitriding and annealing of InSb** L.Haworth, J.Lu, D.I.Westwood and J.E.MacDonald, Applied Surface Science 166 p253 (2000)

Other applications

226. **Reactive ion etching and free radicals.** R Clampitt, T Jolly & P Reader. Semicon Intl - Brighton (1981)
227. **Thin film processing with reactive atom beams.** S Davies, N Barrett, R Clampitt, M Castell & P Allen. Vuoto **XX** (2), pp463 (1990)
228. **AlGaAs microelectronic device processing using an As capping layer.** J Grepstad, H Husby, R Bernstein & B Fimland. MRS 1993 Fall Meeting. Symposium K. (1993)
229. **Growth of Silicon Carbide on (100) Silicon substrates by molecular beam epitaxy.** V.M. Airaksinen, J. Kaitila, H. Niemi, J. Lahtinen and J Saarilahti. Physica Scripta **54**, pp205-207, 1994

RF Solid crackers

230. **Generation of atomic group V materials for the p-type doping of wide II-VI semiconductors using a novel plasma cracker,** H.J.Lugauer, A.Waag, L.Worschech, W.Ossau and G.Landwehr, Journal of Crystal Growth 161 p86 (1996)
231. **P-type doping of wide gap II-VI semiconductors using a novel plasma cracker,** A.Waag, L.Worschech, and G.Landwehr Proceedings of VIII European workshop on molecular beam epitaxy, Granada, Spain (1995)
232. **Doping of ZnSe during molecular beam epitaxial growth using an atomic phosphorus source** L.C.Calhoun and R.M.Park, Journal of Applied Physics 85 p490 (1999)